

| Ref # | Hits | Search Query  | DBs                         | Default Operator | Plurals | Time Stamp       |
|-------|------|---|-----------------------------|------------------|---------|------------------|
| L1    | 70   | (((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate) | US-PGPU B; USPAT            | OR               | ON      | 2005/04/17 17:25 |
| L2    | 0    | (((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate) | USOCR                       | OR               | ON      | 2005/04/17 17:26 |
| L3    | 0    | (((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate) | EPO; JPO; DERWENT ; IBM_TDB | OR               | ON      | 2005/04/17 17:26 |
| L4    | 21   | ((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4) and (etch\$3 near5 rate)   | EPO; JPO; DERWENT ; IBM_TDB | OR               | ON      | 2005/04/17 17:27 |